



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Daijiro INOUE et al.**

Group Art Unit: 2828

Serial No.: 09/746,065

Examiner: **Armando RODRIGUEZ**

Filed: **December 26, 2000**

**P.T.O. Confirmation No.: 1991**

For: **SEMICONDUCTOR LASER DEVICE**

**RESPONSE UNDER 37 C.F.R. §1.116**  
**- EXPEDITED RESPONSE -**  
**GROUP ART UNIT 2828**

**MAILSTOP AF**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

July 9, 2003

Sir:

In response to the Office Action dated February 11, 2003, the response due date herein extended to July 11, 2003 by a two-month Extension of Time, Applicants amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please amend claim 6 as follows:**

6. **(Amended)** The semiconductor laser device according to claim 1, further comprising a ridge-shaped second cladding layer of a first conduction type provided on said depletion enhancement layer in said current injection region, wherein

said depletion enhancement layer is formed on said first cladding layer, and

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said low carrier concentration layer and said current blocking layer are successively formed on said depletion enhancement layer located on both sides of said second cladding layer and on the side surfaces of said second cladding layer.